

Please replace paragraph [0062] beginning on page 37, line 14, with the following rewritten paragraph:

A2 -- Figs. 7a and 7b illustrate circuit diagrams of a power amplification circuit 61 in a sixth embodiment of the invention. In Fig. 7a, this power amplification circuit 61 of the sixth embodiment is made up by using base - emitter junctions of a first bipolar transistor Tr61 and a second bipolar transistor Tr62 in place of the diodes D51, D52 of the power amplification circuit 51 of the fifth embodiment shown in Fig. 6. In this sixth embodiment, Tr61 and Tr62's collectors are short-circuited to their bases, respectively, but those collectors may be in the open state. Also, base - collector junctions of bipolar transistors may be used as the diodes. Further, as shown in Fig. 7b, it is also possible to use field effect transistors in place of the first, second bipolar transistors Tr61, Tr62, where the field effect transistors are connected with their gates, drains and sources corresponding to the bases, collectors and emitters of the first, second bipolar transistors Tr61, Tr62, respectively, and with the gate - source junctions or gate - drain junctions used as the diodes.--

**IN THE CLAIMS:**

Please replace claims 1-4 and 6 with the following amended claims: Please note that claims 1-4 and 6 are presented below in their amended form. They are further presented as an Attachment to the Amendment whereby the amendments to the claims are outlined using the conventional method of bracketing and underlining.

- A3
1. (Amended) A power amplification circuit comprising:  
a power amplifier; and